

M1FL40U

400V 1.5A

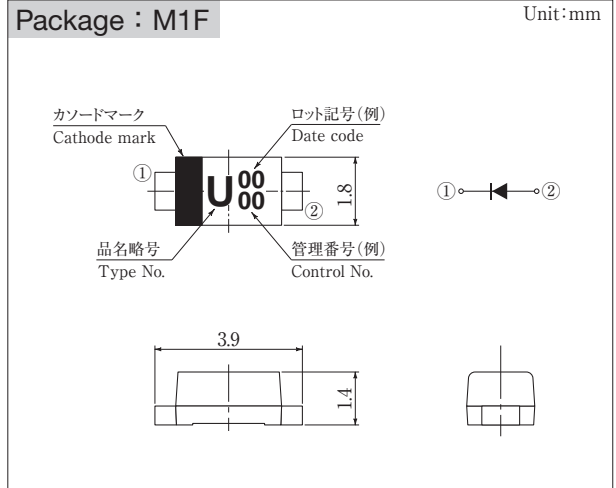
特長

- 高耐圧
- 超高速スイッチング
- 小型SMD

Feature

- High Voltage
- Ultra-High Recovery Speed
- Small SMD

外観図 OUTLINE



外形図については新電元Webサイトをご参照下さい。捺印表示については捺印仕様をご確認下さい。

For details of the outline dimensions, refer to our web site. As for the marking, refer to the specification "Marking, Terminal Connection".

定格表 RATINGS

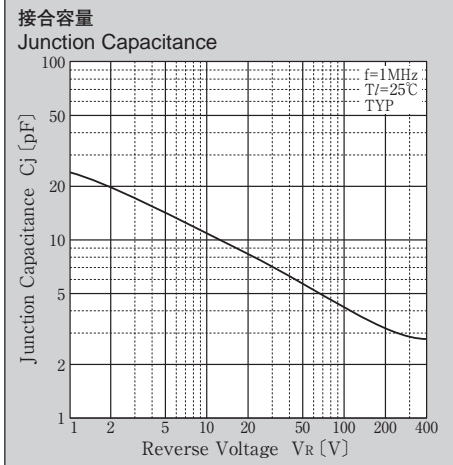
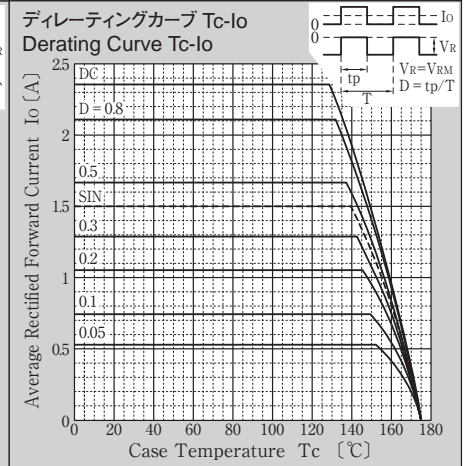
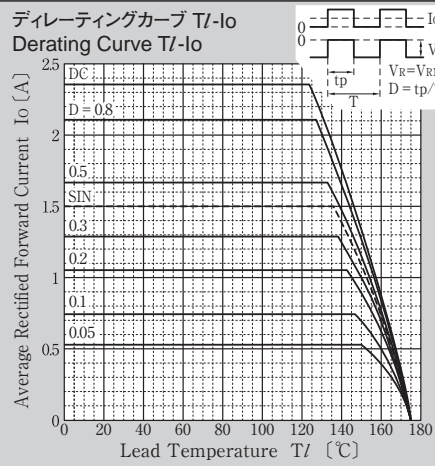
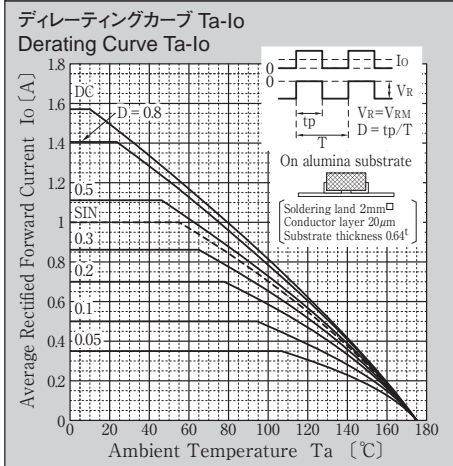
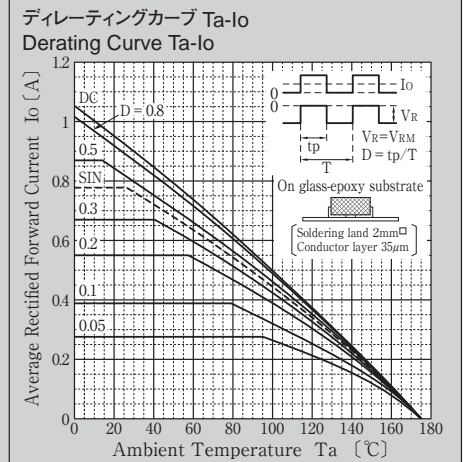
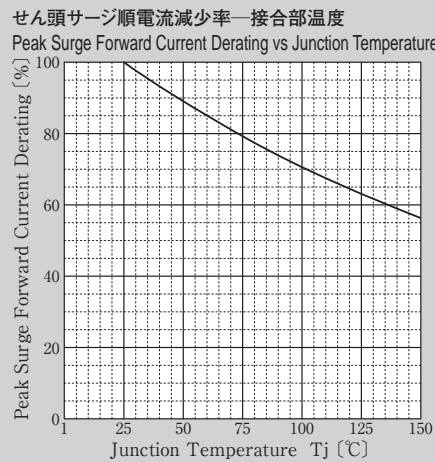
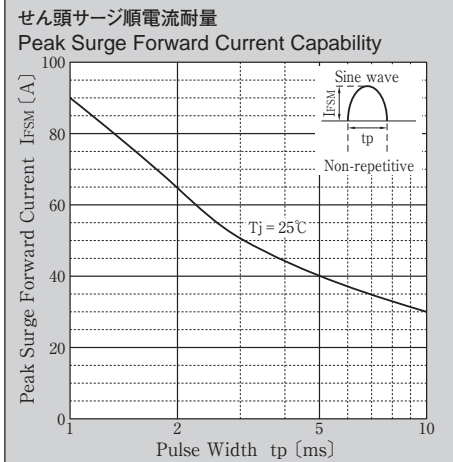
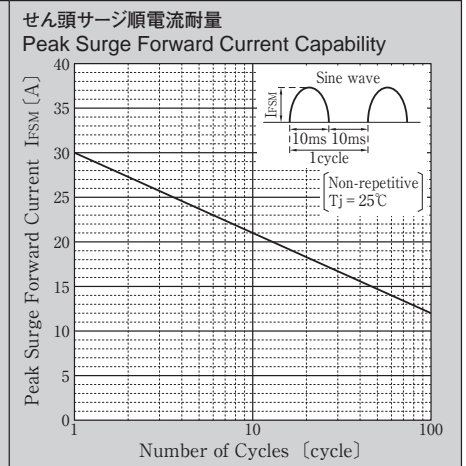
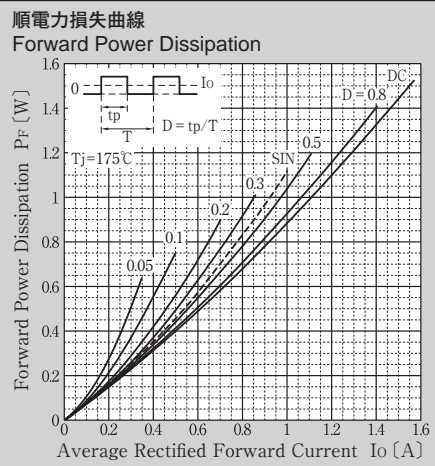
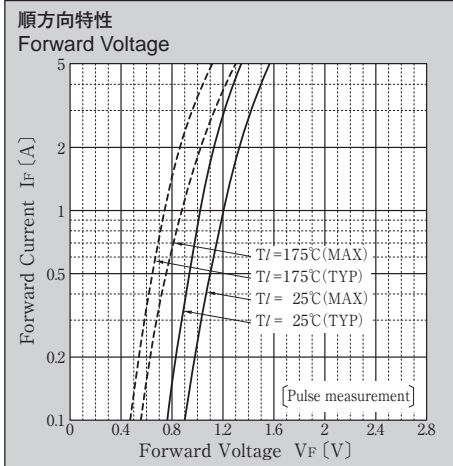
● 絶対最大定格 Absolute Maximum Ratings (指定のない場合 $T_l = 25^\circ\text{C}$ / Unless otherwise specified)

項目 Item	記号 Symbol	条件 Conditions	規格値 Ratings	単位 Unit
保存温度 Storage Temperature	T_{stg}		- 55 ~ 175	$^\circ\text{C}$
接合部温度 Operation Junction Temperature	T_j		175	$^\circ\text{C}$
せん頭逆電圧 Maximum Reverse Voltage	V_{RM}		400	V
出力電流 Average Rectified Forward Current	I_o	50Hz 正弦波, 抵抗負荷, プリント基板実装 $T_a = 25^\circ\text{C}$ 50Hz sine wave, Resistance load, On glass-epoxy substrate $T_a = 25^\circ\text{C}$	0.78	A
		50Hz 正弦波, 抵抗負荷, アルミナ基板実装 $T_a = 54^\circ\text{C}$ 50Hz sine wave, Resistance load, On alumina substrate $T_a = 54^\circ\text{C}$	1.0	
		50Hz 正弦波, 抵抗負荷, $T_l = 135^\circ\text{C}$ 50Hz sine wave, Resistance load, $T_l = 135^\circ\text{C}$	1.5	
		50Hz 正弦波, 抵抗負荷, $T_c = 139^\circ\text{C}$ 50Hz sine wave, Resistance load, $T_c = 139^\circ\text{C}$	1.5	
せん頭サーージ順電流 Peak Surge Forward Current	I_{FSM}	50Hz 正弦波, 非繰り返し1サイクルせん頭値, $T_j = 25^\circ\text{C}$ 50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$	30	A
	I_{FSM1}	$t_p = 1\text{ms}$ 正弦波, 非繰り返し1サイクルせん頭値, $T_j = 25^\circ\text{C}$ $t_p = 1\text{ms}$ 50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$	90	

● 電氣的・熱的特性 Electrical Characteristics (指定のない場合 $T_l = 25^\circ\text{C}$ / Unless otherwise specified)

順電圧 Forward Voltage	V_F	$I_F = 1.0\text{A}$, パルス測定 Pulse measurement	MAX 1.2	V
逆電流 Reverse Current	I_R	$V_R = 400\text{V}$, パルス測定 Pulse measurement	MAX 10	μA
逆回復時間 Reverse Recovery Time	t_{rr}	$I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $0.25 I_R$	MAX 25	ns
接合容量 Junction Capacitance	C_j	$f = 1\text{MHz}$, $V_R = 10\text{V}$	TYP 11	pF
熱抵抗 Thermal Resistance	θ_{ja}	接合部・周囲間, プリント基板実装 Junction to ambient, On glass-epoxy substrate	MAX 186	$^\circ\text{C}/\text{W}$
		接合部・周囲間, アルミナ基板実装 Junction to ambient, On alumina substrate	MAX 108	
	θ_{jl}	接合部・リード間 Junction to lead	MAX 20	
	θ_{jc}	接合部・ケース間 Junction to case	MAX 18	

■特性図 CHARACTERISTIC DIAGRAMS



* Sine waveは50Hzで測定しています。
* 50Hz sine wave is used for measurements.